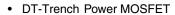


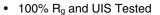
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# P-Channel 60 V (D-S) MOSFET

| PRODUCT SUMMARY     |                                    |       |  |  |  |
|---------------------|------------------------------------|-------|--|--|--|
| V <sub>DS</sub> (V) | $V_{DS}(V)$ $R_{DS(on)}(\Omega)$   |       |  |  |  |
| - 60                | 0.158 at V <sub>GS</sub> = - 10 V  | - 12  |  |  |  |
| - 00                | 0.210 at V <sub>GS</sub> = - 4.5 V | - 8.7 |  |  |  |

#### **FEATURES**

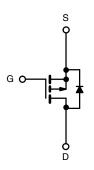






#### **APPLICATIONS**

- Load Switch
- · Notebook Adaptor Switch



P-Channel MOSFET

| TO-252 |            |         |  |  |
|--------|------------|---------|--|--|
|        |            | <u></u> |  |  |
|        | $\bigcirc$ |         |  |  |
|        |            | $\prod$ |  |  |
| G      | D          | S       |  |  |
| Т      | op Vie     | w       |  |  |

| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted) |                         |                                   |                     |      |  |
|---|-------------------------|-----------------------------------|---------------------|------|--|
| Parameter   | Symbol                  | Limit                             | Unit                |      |  |
| Drain-Source Voltage  |                         | V <sub>DS</sub>                   | - 60                | V    |  |
| Gate-Source Voltage   |                         | V <sub>GS</sub> ± 20              |                     | ¬    |  |
| Continuous Drain Current (T <sub>.1</sub> = 175 °C)                       | T <sub>C</sub> = 25 °C  | I_                                | - 12 <sup>d</sup>   | Α    |  |
| Continuous Brain Current (1j = 175 C)                                     | T <sub>C</sub> = 125 °C | I <sub>D</sub>                    | - 9.2               |      |  |
| Pulsed Drain Current  | I <sub>DM</sub>         | - 48                              | 7                   |      |  |
| Avalanche Current   | I <sub>AS</sub>         | - 15                              |                     |      |  |
| Single Pulse Avalanche Energy <sup>a</sup>                                | L = 0.1 mH              | E <sub>AS</sub>                   | 25                  | mJ   |  |
| Power Dissipation   | T <sub>C</sub> = 25 °C  | P <sub>D</sub>                    | 50°                 | W    |  |
| Fower Dissipation   | T <sub>A</sub> = 25 °C  | ' D                               | 2.7 <sup>b, c</sup> | 7 ** |  |
| Operating Junction and Storage Temperature Range                          |                         | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150         | °C   |  |

| THERMAL RESISTANCE RATINGS       |              |                     |         |         |      |  |
|----------------------------------|--------------|---------------------|---------|---------|------|--|
| Parameter                        |              | Symbol              | Typical | Maximum | Unit |  |
| Junction-to-Ambient <sup>b</sup> | t ≤ 10 s     | - R <sub>thJA</sub> | 20      | 25      | °C/W |  |
| Junction-to-Ambient              | Steady State |                     | 65      | 75      |      |  |
| Junction-to-Case                 |              | R <sub>thJC</sub>   | 4.5     | 7.1     |      |  |

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



| Parameter                                     | Symbol              | Test Conditions   | Min. | Тур.  | Max.  | Unit |  |
|---|---------------------|---|------|-------|-------|------|--|
| Static  |                     |   |      |       |       |      |  |
| Drain-Source Breakdown Voltage                | V <sub>DS</sub>     | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$                            | - 60 |       |       | V    |  |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$                                     | - 1  |       | - 3   | V    |  |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                         |      |       | ± 100 | nA   |  |
|   |                     | V <sub>DS</sub> = - 48 V, V <sub>GS</sub> = 0 V                           |      |       | - 1   |      |  |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> = - 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C  |      |       | - 50  | μΑ   |  |
|   |                     | V <sub>DS</sub> = - 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C  |      |       | - 100 | 1    |  |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>  | V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V                         | - 12 |       |       | Α    |  |
|   |                     | V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 8 A                          |      | 0.158 | 0.175 | 5    |  |
|   | B                   | V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 8 A, T <sub>J</sub> = 125 °C |      |       | 0.238 | 0    |  |
| Drain-Source On-State Resistance <sup>a</sup> | R <sub>DS(on)</sub> | V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 8 A, T <sub>J</sub> = 150 °C |      |       | 0.259 |      |  |
|   |                     | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A                         |      | 0.210 | 0.252 |      |  |
| Forward Transconductance <sup>a</sup>         | 9 <sub>fs</sub>     | V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 8 A                           |      | 11    |       | S    |  |
| Dynamic <sup>b</sup>                          |                     |   |      | •     |       |      |  |
| Input Capacitance                             | C <sub>iss</sub>    |   |      | 625   |       |      |  |
| Output Capacitance                            | C <sub>oss</sub>    | $V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$         |      | 110   |       | pF   |  |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>    |   |      | 55    |       |      |  |
| Total Gate Charge <sup>c</sup>                | $Q_g$               |   |      | 20    | 29    |      |  |
| Gate-Source Charge <sup>c</sup>               | $Q_{gs}$            | $V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -8 \text{ A}$    |      | 12    |       | nC   |  |
| Gate-Drain Charge <sup>c</sup>                | $Q_{gd}$            |   |      | 13    |       |      |  |
| Turn-On Delay Time <sup>c</sup>               | t <sub>d(on)</sub>  |   |      | 11    |       |      |  |
| Rise Time <sup>c</sup>                        | t <sub>r</sub>      | $V_{DD} = -30 \text{ V}, R_{L} = 0.6 \Omega$                              |      | 15    |       | 20   |  |
| Turn-Off Delay Time <sup>c</sup>              | t <sub>d(off)</sub> | $I_D \cong -8 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6 \Omega$         |      | 35    |       | ns   |  |
| Fall Time <sup>c</sup>                        | t <sub>f</sub>      |   |      | 15    |       |      |  |
| Source-Drain Diode Ratings and Cha            | racteristics -      | Γ <sub>C</sub> = 25 °C <sup>b</sup>                                       |      |       |       |      |  |
| Continuous Current                            | I <sub>S</sub>      |   |      |       | - 12  | ۸    |  |
| Pulsed Current                                | I <sub>SM</sub>     |   |      |       | - 48  | Α    |  |
| Forward Voltage <sup>a</sup>                  | V <sub>SD</sub>     | I <sub>F</sub> = -8 A, V <sub>GS</sub> = 0 V                              |      | - 1   | - 1.6 | V    |  |
| Reverse Recovery Time                         | t <sub>rr</sub>     | I <sub>F</sub> = - 8 A, dI/dt = 100 A/μs                                  |      | 25    | 33    | ns   |  |

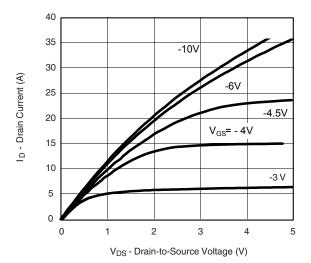
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing. c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

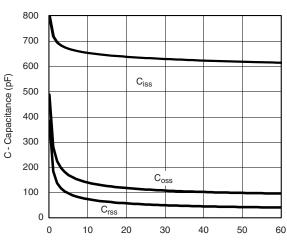




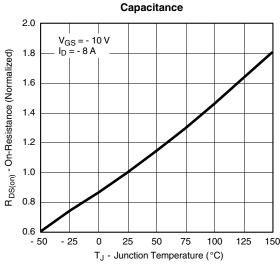
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



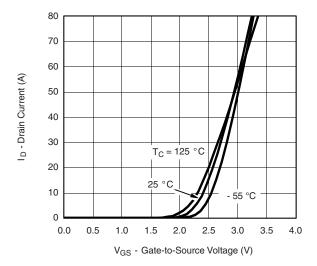
#### **Output Characteristics**



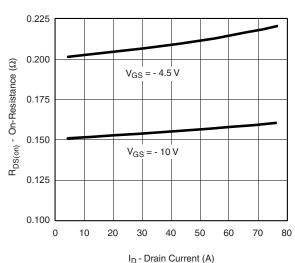
 $V_{DS}$  - Drain-to-Source Voltage (V)



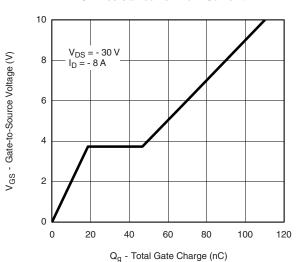
On-Resistance vs. Junction Temperature



**Transfer Characteristics** 



**On-Resistance vs. Drain Current** 

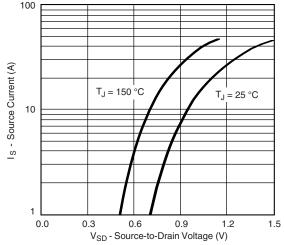


Gate Charge

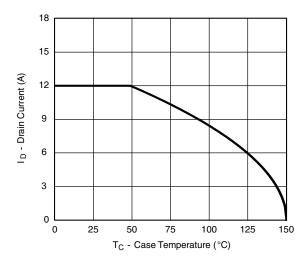


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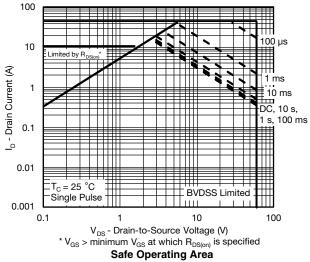
#### **TYPICAL CHARACTERISTICS**



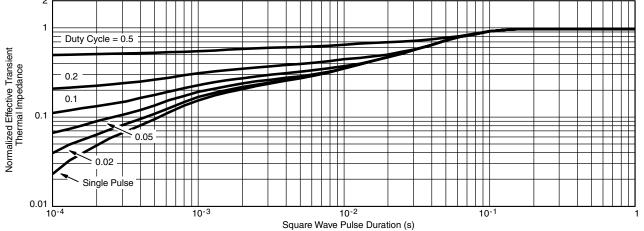
Source-Drain Diode Forward Voltage



**Drain Current vs. Case Temperature** 



Safe Operating Area

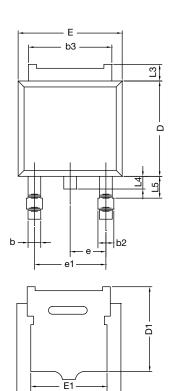


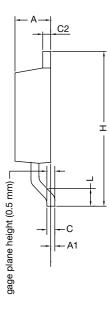
Normalized Thermal Transient Impedance, Junction-to-Case





# **TO-252AA CASE OUTLINE**





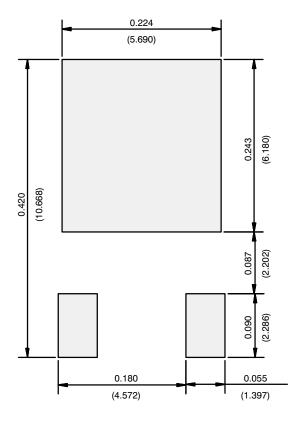
|                                 | MILLIN   | METERS   | INCHES    |       |  |
|---------------------------------|----------|----------|-----------|-------|--|
| DIM.                            | MIN.     | MAX.     | MIN.      | MAX.  |  |
| Α                               | 2.18     | 2.38     | 0.086     | 0.094 |  |
| A1                              | -        | 0.127    | -         | 0.005 |  |
| b                               | 0.64     | 0.88     | 0.025     | 0.035 |  |
| b2                              | 0.76     | 1.14     | 0.030     | 0.045 |  |
| b3                              | 4.95     | 5.46     | 0.195     | 0.215 |  |
| С                               | 0.46     | 0.61     | 0.018     | 0.024 |  |
| C2                              | 0.46     | 0.89     | 0.018     | 0.035 |  |
| D                               | 5.97     | 6.22     | 0.235     | 0.245 |  |
| D1                              | 5.21     | -        | 0.205     | -     |  |
| Е                               | 6.35     | 6.73     | 0.250     | 0.265 |  |
| E1                              | 4.32     | -        | 0.170     | -     |  |
| Н                               | 9.40     | 10.41    | 0.370     | 0.410 |  |
| е                               | 2.28     | 2.28 BSC |           | BSC   |  |
| e1                              | 4.56 BSC |          | 0.180 BSC |       |  |
| L                               | 1.40     | 1.78     | 0.055     | 0.070 |  |
| L3                              | 0.89     | 1.27     | 0.035     | 0.050 |  |
| L4                              | -        | 1.02     | -         | 0.040 |  |
| L5                              | 1.14     | 1.52     | 0.045     | 0.060 |  |
| ECN: X12-0247-Rev. M, 24-Dec-12 |          |          |           |       |  |

### DWG: 5347 Note

• Dimension L3 is for reference only.



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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